



Description

The XPX2080FD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

$V_{DS} = 20V, I_D = 85A$

$R_{DS(ON)} = 2.8m\Omega$ (typ) @ $V_{GS} = 4.5V$

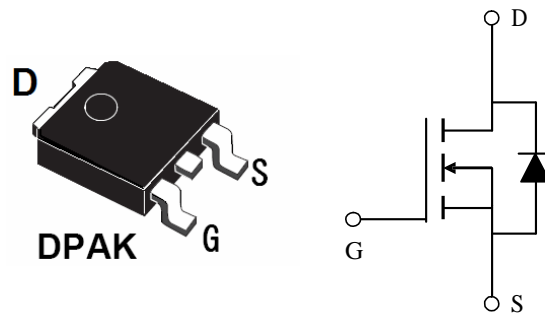
$R_{DS(ON)} = 4m\Omega$ (typ) @ $V_{GS} = 2.5V$

General Features

- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2080	XPX2080FD	TO-252-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 12	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	85	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	62	A
IDM	Pulsed Drain Current ^{note1}	380	A
EAS	Single Pulsed Avalanche Energy ^{note2}	110	mJ
P_D	Power Dissipation	83	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.95	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$

Electrical Characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	22	-	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	-	-	1	μA
IGSS	Gate to Body Leakage Current	V _{GS} = ±12V, V _{DS} =0V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.68	1.0	V
RDS(on)	Static Drain-Source On-Resistance note3	V _{GS} =4.5V, I _D =30A	-	2.8	3.5	mΩ
		V _{GS} =2.5V, I _D =20A		4	6	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz	-	3200	-	pF
C _{oss}	Output Capacitance		-	460	-	pF
C _{rss}	Reverse Transfer Capacitance		-	445	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =30A, V _{GS} =4.5V	-	48	-	nC
Q _{gs}	Gate-Source Charge		-	3.6	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	19	-	nC
td(on)	Turn-On Delay Time	V _{DS} =10V, I _D =30A, R _G =1.8Ω, V _{GS} =4.5V	-	9.7	-	ns
t _r	Turn-On Rise Time		-	37	-	ns
td(off)	Turn-Off Delay Time		-	63	-	ns
t _f	Turn-Off Fall Time		-	52	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	90	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	360	A
VSD	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _{SD} =30A, T _J =25°C	-	-	1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C, I _F =30A, di/dt =100A/μs	-	23	-	ns
Q _{rr}	Reverse Recovery Charge		-	10	-	nC

Note :

- 1、 The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、 The EAS condition: T_J=25°C, V_{DD}=15V, V_G=4.5V, R_G=25Ω, L=0.5mH, I_{AS}=21A
- 4、 The power dissipation is limited by 175°C junction temperature
- 5、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

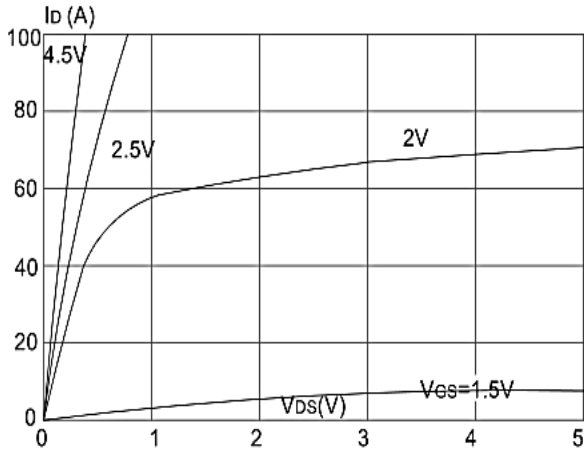


Figure1: Output Characteristics

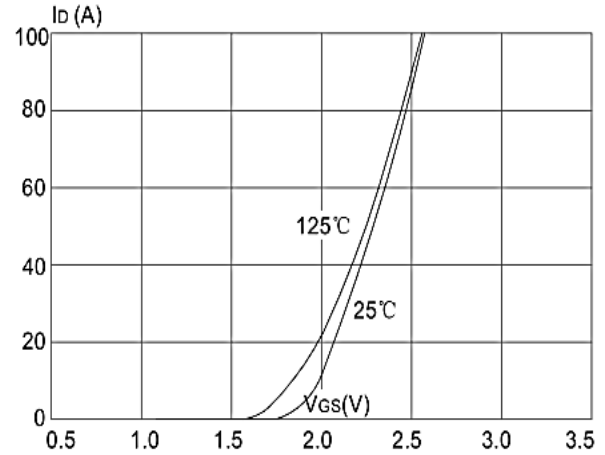


Figure 2: Typical Transfer Characteristics

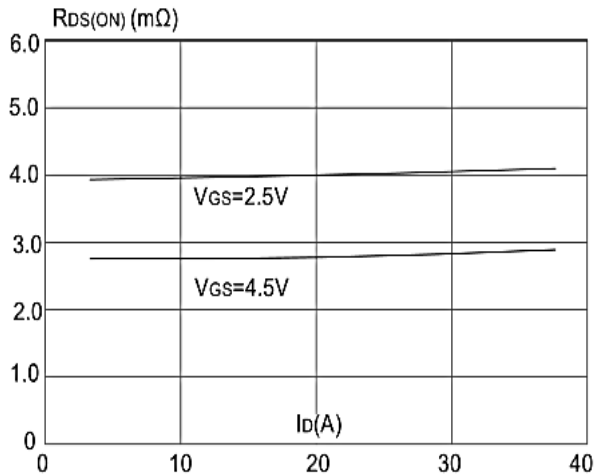


Figure 3: On-resistance vs. Drain Current

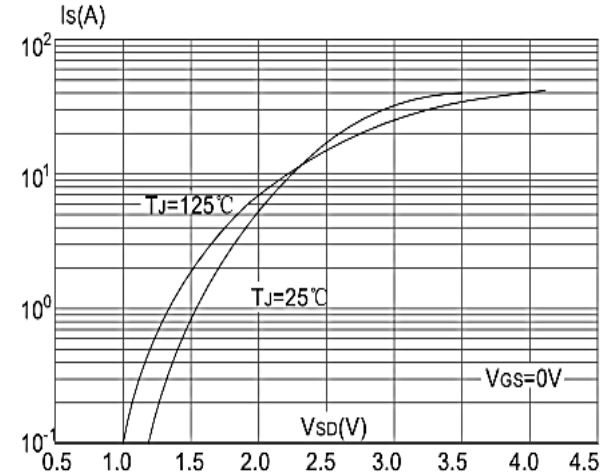


Figure 4: Body Diode Characteristics

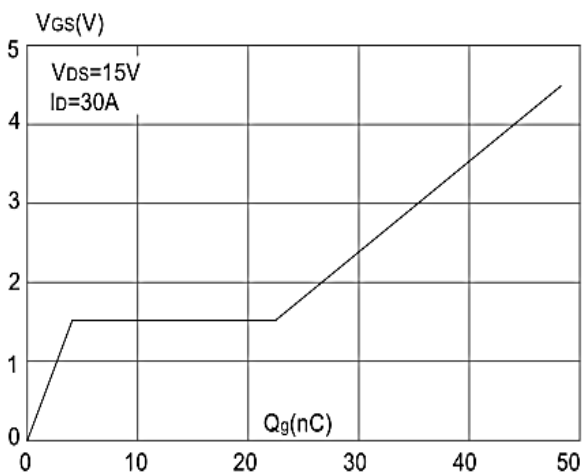


Figure 5: Gate Charge Characteristics

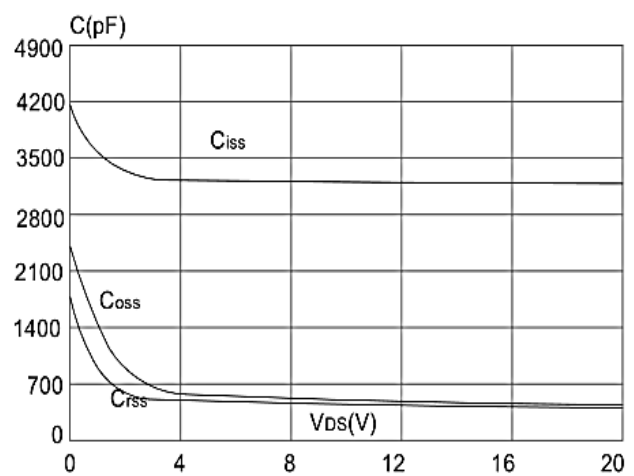


Figure 6: Capacitance Characteristics

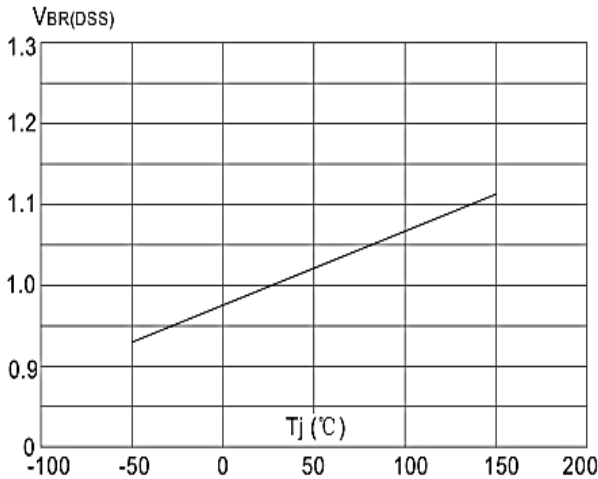


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

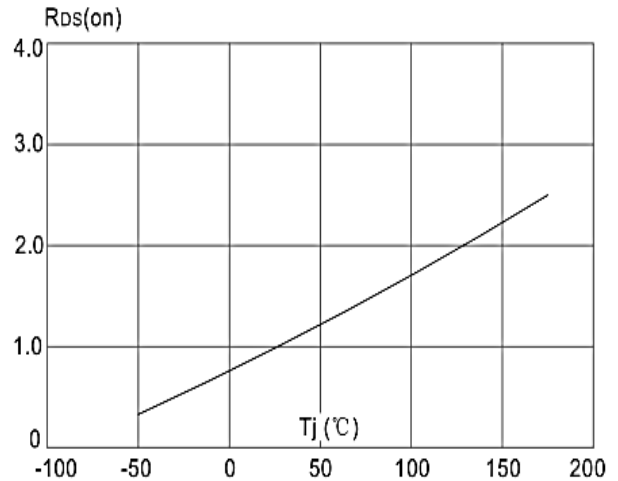


Figure 8: Normalized on Resistance vs. Junction Temperature

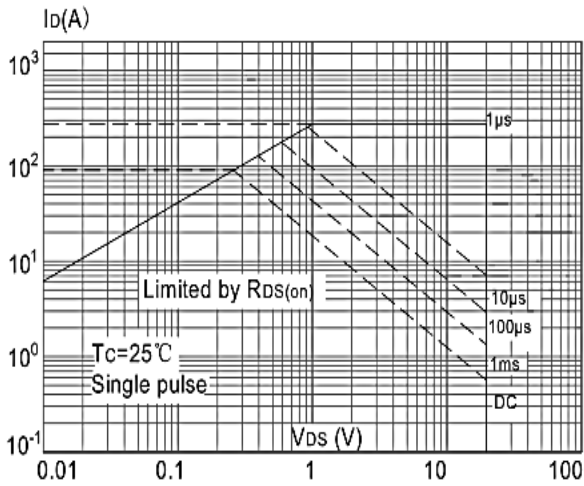


Figure 9: Maximum Safe Operating Area

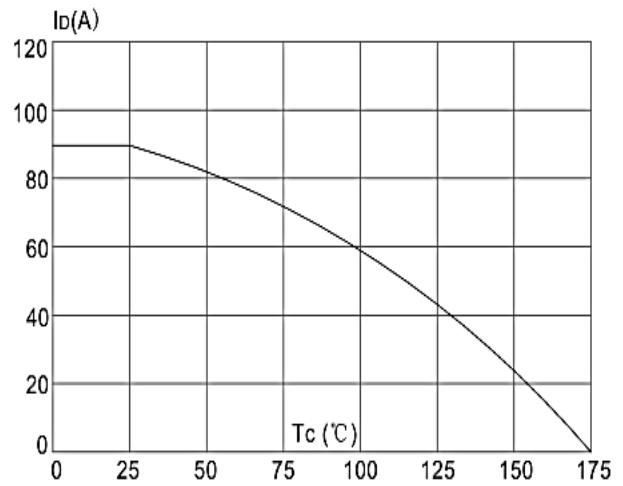


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

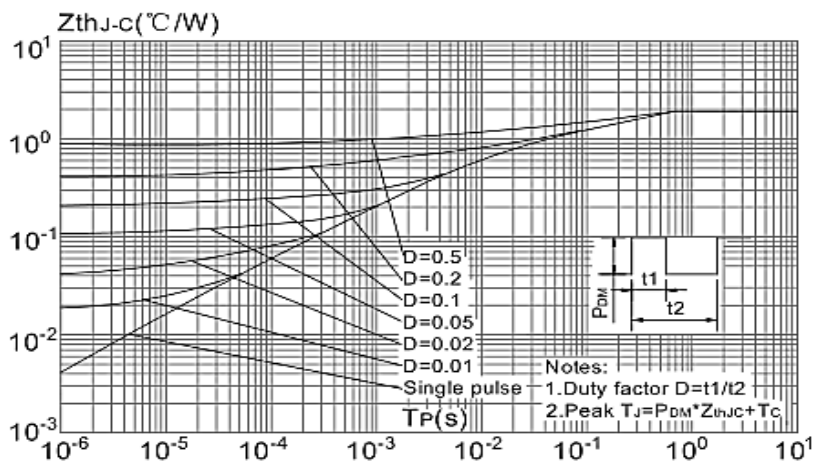
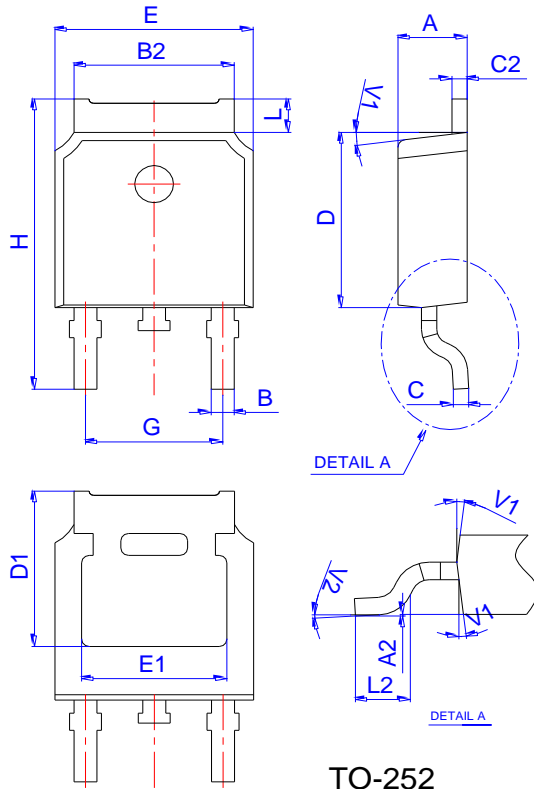
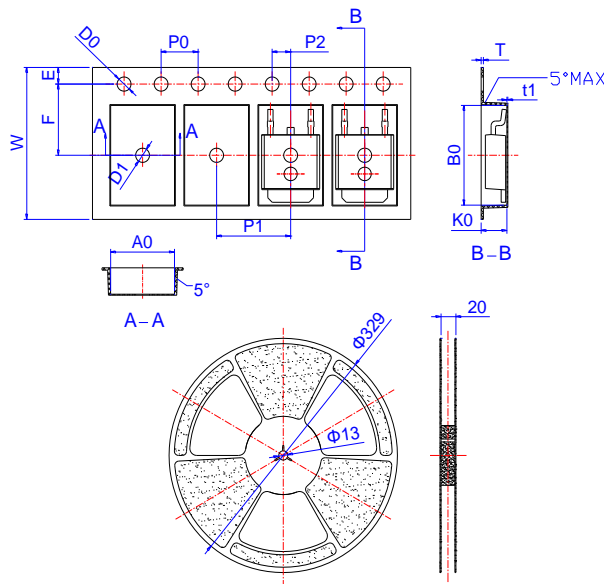


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

Package Mechanical Data:TO-252-3L


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec±1sec
Pb-Free device	260°C +0/-5°C	5sec±1sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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